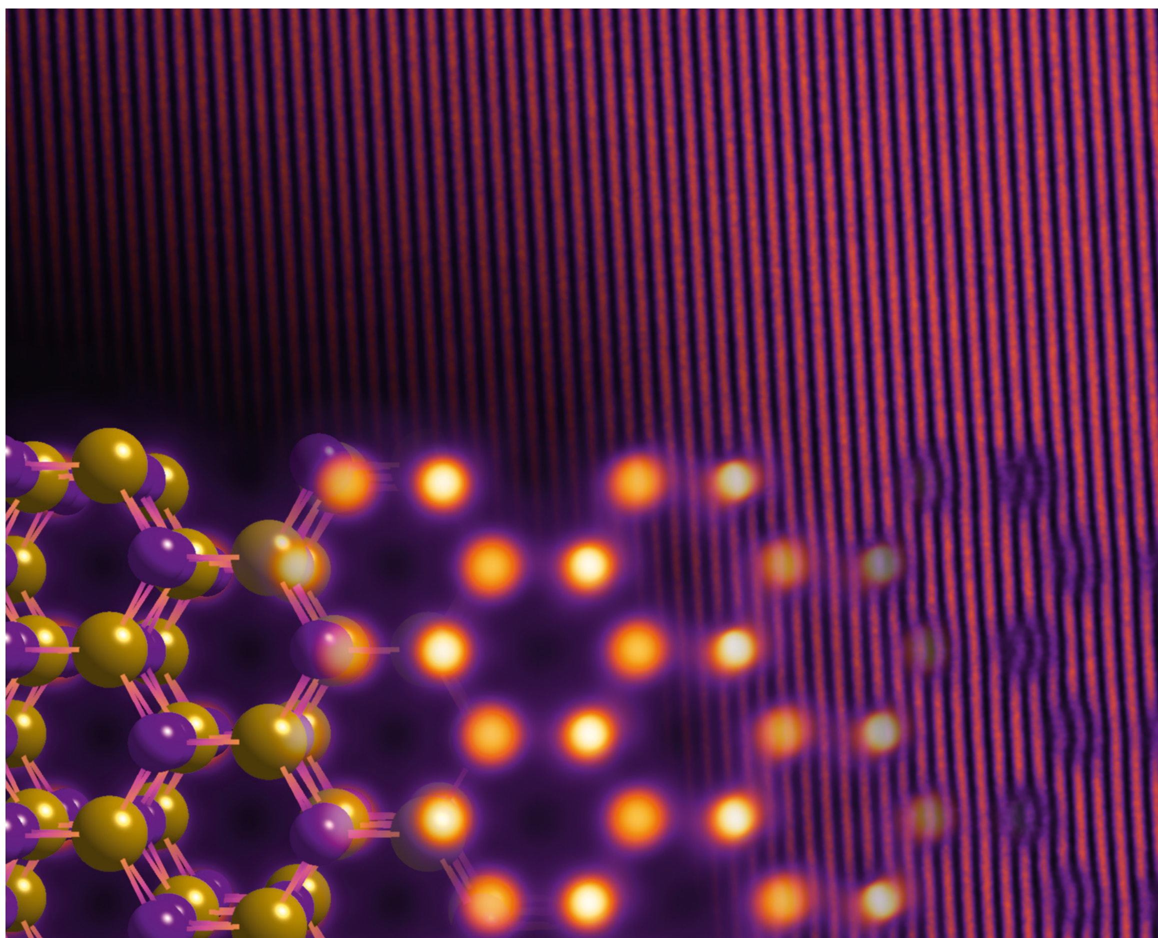

Absolute scale off-axis electron holography of thin dichalcogenide crystals at atomic resolution

Florian Winkler

Schlüsseltechnologien / Key Technologies
Band / Volume 191
ISBN 978-3-95806-383-9

Mitglied der Helmholtz-Gemeinschaft

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Schriften des Forschungszentrums Jülich
Reihe Schlüsseltechnologien / Key Technologies Band / Volume 191

ISSN 1866-1807 ISBN 978-3-95806-383-9

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